SAMYO

No. × 4819

LC36256ALL, AMLL-70W/85W/10W/12W

256 K (32768 words × 8 bits) SRAM

Preliminary

Overview

The LC36256ALL, AMLL-70W/85W/10W/12W are fully asynchronous silicon gate CMOS static RAMs with an 32,768 words × 8 bits.

This series has \overline{CE} chip enable pin for device select/nonselect control and an \overline{OE} output enable pin for output control, and features high speed, low power dissipation, and wide temperature range.

Current dissipation is notably reduced during standby and data retention. For these reasons, this series is most suited for use in systems requiring high speed, low power dissipation, and long-term battery backup. Simple memory capacity expansion is also supproted.

Features

· Access time

70 ns (max.): LC36256ALL-70W,

LC36256AMLL-70W

85 ns (max.): LC36256ALL-85W,

LC36256AMLL-85W

100 ns (max.): LC36256ALL-10W,

LC36256AMLL-10W

120 ns (max.): LC36256ALL-12W,

LC36256AMLL-12W

· Low current dissipation

During standby

 $0.5 \, \mu A \, (max.) / Ta = 25^{\circ} C$

1 $\mu A \text{ (max.)} / \text{Ta} = -10 \text{ to } +40^{\circ}\text{C}$

5 μ A (max.) / Ta = -10 to +70°C

During data retention

 $0.3 \mu A \text{ (max.)} / \text{Ta} = 25^{\circ}\text{C}$

 $0.6 \,\mu\text{A} \,(\text{max.}) \,/\,\text{Ta} = -10 \text{ to } +40^{\circ}\text{C}$

3 $\mu A (max.) / Ta = -10 \text{ to } +70^{\circ}C$

During operation (DC)

10 mA (max.)

• Single 5 V power supply: 5 V ± 10%

Data retention power supply voltage: 2.0 to 5.5 V

• No clock required (Fully static memory)

· All input/output levels are TTL compatible

• Common input/output pins, with three output states

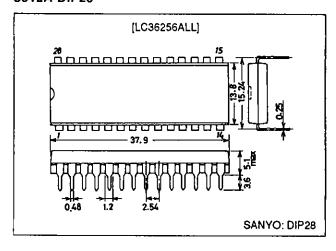
Packages

DIP 28-pin plastic package (600 mil) : LC36256ALL SOP 28D-pin plastic package (450 mil): LC36256AMLL

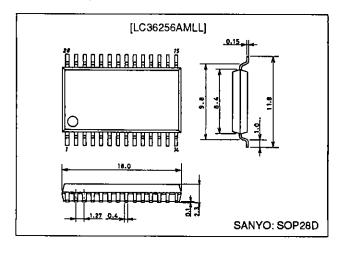
Package Dimensions

unit: mm

3012A-DIP28

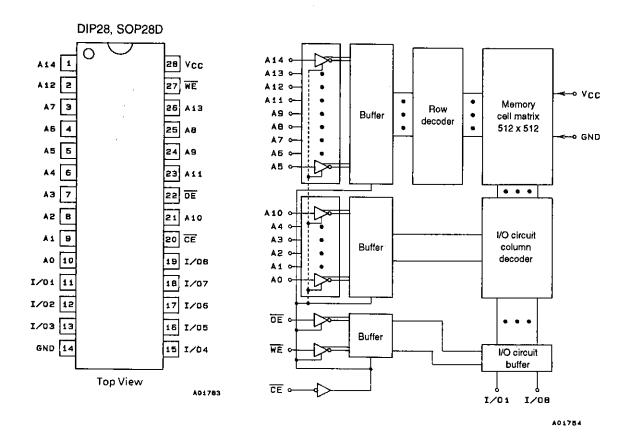


3187-SOP28D



Pin Assignment

Block Diagram



Pin Functions

A ₀ to A ₁₄	Address input
WE	Read/write control input
ŌĒ	Output enable input
CE	Chip enable input
I/O ₁ to I/O ₈	Data input/output
V _{CC} , GND	Power supply pins

Functions Logic

Mode	CE	ŌĒ	WE	1/0	Supply current
Read cycle	L	L	н	Data output	ICCA
Write cycle	L	Х	L	Data input	Icca
Output disable	L	Н	Н	High impedance	ICCA
Nonselect	н	Х	Х	High impedance	Iccs

X: H or L

Specifications

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit	
Maximum supply voltage	V _{CC} max		7.0	٧	
Input pin voltage	V _{IN}		-0.5* to V _{CC} + 0.5	V	
I/O pin voltage	V _{I/O}		-0.5* to V _{CC} + 0.5	٧	
Allowable power dissipation	Pd max	LC36256ALL	1.0	W	
Allowable power dissipation	Po max	LC36256AMLL	0.7	W	
Operating temperature range	Topr		-10 to +70	°C	
Storage temperature range	Tstg	-	-55 to +150	°C	

^{* -3.0} V when pulse width is less than 50 ns

DC Recommended Operating Ranges at $Ta = -10 \text{ to } +70^{\circ}\text{C}$

Parameter	Symbol	min	typ	max	Unit
Power supply voltage	V _{CC}	4.5	5.0	5.5	٧
Input high level voltage	V _{IH}	2.2		V _{CC} + 0.3	٧
Input low level voltage	V _{IL}	-0.3*		+0.8	٧

 ^{−3.0} V when pulse width is less than 50 ns

DC Electrical Characteristics at Ta = –10 to +70°C, V_{CC} = 5 $V\pm10\,\%$

Parameter	Symbol	Coi	min	typ*	max	Unit		
Input leakage current	ILi	V _{IN} = 0 to V _{CC}	-0.5		+0.5	μА		
I/O leakage current	lLO	VCE = VIH or VOE = VIH,	-0.5	-	+0.5	μА		
Output high level voltage	V _{OH}	I _{OH} = -1.0 mA	2.4		•	v		
Output low level voltage	V _{OL}	I _{OL} = 2.1 mA			0.4	V		
Operating supply current (DC)	I _{CCA1}	$V_{\overline{CE}} \le 0.2 \text{ V}, V_{ N } \le 0.2 \text{ V}$ $I_{ /O} = 0 \text{ mA}$		1	5	mA		
	I _{CCA2}	V _{CE} = V _{IL} , I _{I/O} = 0 mA			3	10	mA	
		min cycle Duty = 100% I _{I/O} = 0 mA		70 ns		30	50	
Average operating supply current			Access	85 ns		25	50	1
Average operating supply current	CCA3		time	100 ns		23	50	mA
				120 ns	•	20	50	1
				-10 to +70°C			5	
Standby supply current	I _{CCS1}	V _{CE} ≥ V _{CC} - 0.2 V		-10 to +40°C			1	μΑ
Standby supply current				25°C		0.2	0.5	1
	I _{CCS2}	VCE = VIH	VCE = VIH			0.4	2	mA

^{*} Reference values at V_{CC} = 5 V, Ta = 25°C

Input/Output Capacitance at Ta = 25°C, f = 1 MHz

Parameter	Symbol	Conditions	min	typ	max	Unit
Input/output capacitance	C _{I/O}	V _{I/O} = 0 V			8	рF
Input capacitance	C _{IN}	V _{IN} = 0 V			6	pF

These parameters were obtained through sampling, and not full-lot measurement.

AC Electrical Characteristics at Ta = –10 to +70°C, V_{CC} = 5 $V\pm10\,\%$

AC testing conditions

Input pulse voltage level

: 0.8 V, 2.2 V

Input rise and fall time

: 5 ns

Input - output timing level : 1.5 V

Output load

: 1 TTL gate + C_L = 100 pF (85 ns/100 ns/120 ns)

1 TTL gate + C_L = 30 pF (70 ns) (including scope and jig capacitance)

Read Cycle

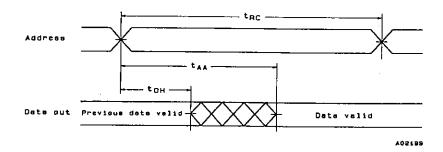
Parameter	Symbol	LC36256ALL-70W LC36256AMLL-70W		LC36256ALL-85W LC36256AMLL-85W		LC36256ALL-10W LC36256AMLL-10W		LC36256ALL-12W LC36256AMLL-12W		Unit
		min	max	min	max	min	max	min	max	
Read cycle time	t _{RC}	70		85		100		120		ns
Address access time	†AA		70		85		100		120	ns
CE access time	t _{CA}		70		85		100		120	ns
OE access time	tод		35		45		50		60	ns
Output hold time	tон	20		20		20	ļ	20		ns
CE output enable time	tco∈	10		10		10		10		ns
OE output enable time	100E	5		5		5	· · · · ·	5		ns
CE output disable time	t _{COD}	0	30	0	30	0	30	0	30	ns ·
OE output disable time	t000	0	30	0	30	.0	30	0	30	ns

Write Cycle

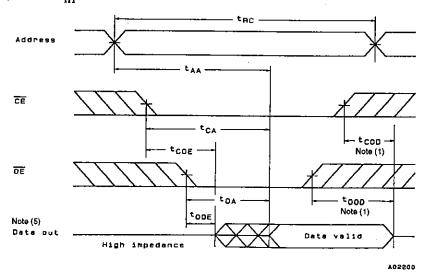
Parameter	Symbol	LC36256ALL-70W LC36256AMLL-70W		LC36256ALL-85W LC36256AMLL-85W		LC36256ALL-10W LC36256AMLL-10W		LC36256ALL-12W LC36256AMLL-12W		Unit
	[min	max	min	max	min	max	min	max	1
Write cycle time	twc	70		85		100	<u> </u>	120		ns
Address valid to end of write	t _{AW}	65		75		80		100		ns
Address setup time	las	0		0		0		0		ns
Write pulse width	t _{WP}	50		50		60		70		ns
CE setup time	t _{CW}	65		75	_	80		100	-	ns
Write recovery time (WE)	twa	0		0		0		0		ns
Write recovery time (CE)	t _{WR1}	0		0	†	0		0		ns
Data setup time	t _{DS}	30		30	<u> </u>	35		40		ns
Data hold time	tон	0		0		0		0		ns
WE output enable time	twoE	10		10		10		10		пѕ
WE output disable time	twop	0	25	0	25	0	25	0	25	ns

Timing Chart

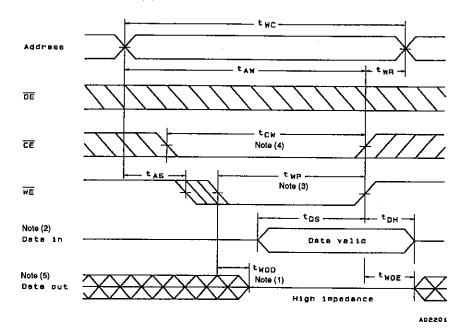
• Read Cycle (1): $\overline{CE} = \overline{OE} = V_{IL}$, $\overline{WE} = V_{IH}$



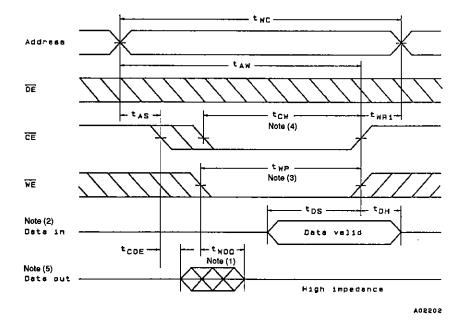
• Read Cycle (2): $\overline{WE} = V_{IH}$



• Write Cycle (1): WE Control Note (6)



• Write Cycle (2): CE Control Note (6)



- Notes: (1) t_{COD}, t_{OOD}, and t_{WOD} are defined as the time at which the outputs becomes the high impedance state and are not referred to output voltage levels.
 - (2) An external antiphase signal must not be applied when D_{OUT} is in the output state.
 - (3) t_{WP} is the time interval that \overline{CE} and \overline{WE} are low-level and is defined as the interval from the falling of \overline{WE} to the rising of \overline{CE} or \overline{WE} whichever is earlier.
 - (4) t_{CW} is the time interval that \overline{CE} and \overline{WE} are low-level and is defined as the time from the falling of \overline{CE} to the rising of \overline{CE} or \overline{WE} , whichever is earlier.
 - (5) D_{OUT} goes to the high-impedance state when either \overline{OE} is high-level, \overline{CE} is high-level, or \overline{WE} is low-level.
 - (6) When \overline{OE} is high-level during the write cycle, D_{OUT} goes to the high-impedance state.

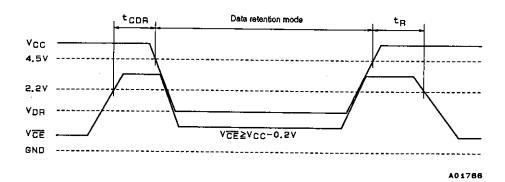
Data Retention Characteristics at $Ta = -10 \text{ to } +70^{\circ}\text{C}$

Parameter	Symbol	Conditions	min	typ*1	max	Unit	
Data retention supply voltage	V _{DR}	V _{CE} ≥ V _{CC} - 0.2 V	2.0		5.5	V	
_	I _{CCDR1}	V _{CC} = 3.0 V, V _{CE} ≥ 2.8 V	-10 to +70°C			3 0.6	
			-10 to +40°C				1 μA
Data retention supply current			25°C		0.1	0.3	1
	ICCDR2	V _{CC} = 2.0 to 5.5 V, V _{CE} ≥ V _{CC} ~ 0.2 V			0.2	5	μА
CE setup time	t _{CDR}			0			ns
CE hold time	t _A			t _{RC} *2			ns

^{* 1.} Reference values at V_{CC} = 5 V, Ta = 25°C

^{* 2.} t_{RC} = Read Cycle time

Data Retention Waveform



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